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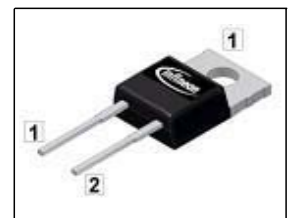


**Fast Switching Diode
Features**

- 600 V diode technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- Easy paralleling
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Qualified according to JEDEC for target applications

Product Summary

V_{RRM}	600	V
I_F	23	A
V_F	1.5	V
T_{jmax}	175	°C

PG-TO220-2


Type	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
IDP23E60	PG-TO220-2	-	D23E60	C	A	-

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	600	V
Continuous forward current	I_F		A
$T_C=25\text{ °C}$		41	
$T_C=90\text{ °C}$		28	
Surge non repetitive forward current	I_{FSM}	89	
$T_C=25\text{ °C}$, $t_p=10\text{ ms}$, sine halfwave			
Maximum repetitive forward current	I_{FRM}	65	
$T_C=25\text{ °C}$, t_p limited by T_{jmax} , $D=0.5$			
Power dissipation	P_{tot}		W
$T_C=25\text{ °C}$		115	
$T_C=90\text{ °C}$		65	
Operating and storage temperature	T_j, T_{stg}	-55... +175	°C
Soldering temperature	T_S	260	°C
wavesoldering, 1.6mm (0.063 in.) from case for 10s			

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	1.3	K/W
SMD version, device on PCB:	R_{thJA}	-	-	75	
@ min. footprint @ 6 cm ² cooling area ¹⁾		-	-	50	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Reverse leakage current $V_R=600V, T_j=25\text{ °C}$ $V_R=600V, T_j=150\text{ °C}$	I_R	-	-	50 1900	μA
Forward voltage drop $I_F=23A, T_j=25\text{ °C}$ $I_F=23A, T_j=150\text{ °C}$	V_F	-	1.5 1.5	2 -	

⁰J-STD20 and JESD22

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

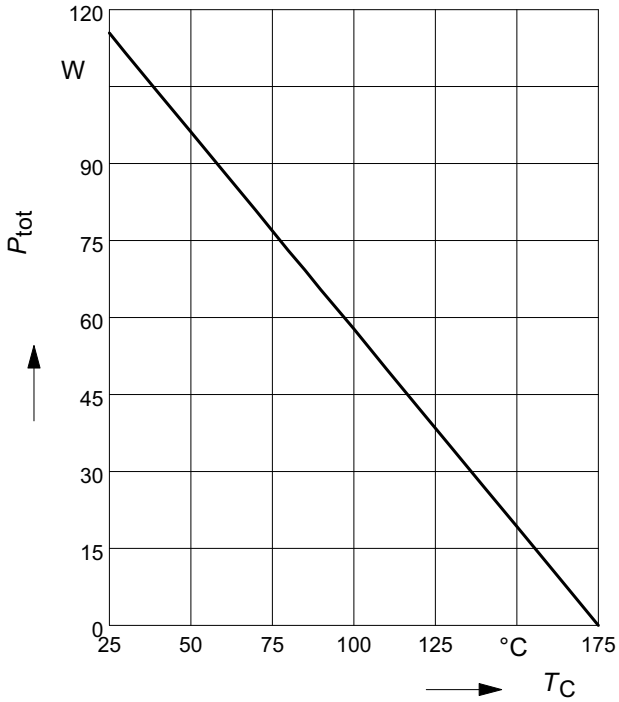
Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Reverse recovery time $V_R=400\text{V}$, $I_F=23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=25\text{°C}$ $V_R=400\text{V}$, $I_F=23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=125\text{°C}$ $V_R=400\text{V}$, $I_F=23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=150\text{°C}$	t_{rr}	-	120	-	ns
Peak reverse current $V_R=400\text{V}$, $I_F = 23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=25\text{°C}$ $V_R=400\text{V}$, $I_F = 23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=125\text{°C}$ $V_R=400\text{V}$, $I_F = 23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=150\text{°C}$	I_{rrm}	-	17	-	A
Reverse recovery charge $V_R=400\text{V}$, $I_F=23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=25\text{°C}$ $V_R=400\text{V}$, $I_F = 23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=125\text{°C}$ $V_R=400\text{V}$, $I_F = 23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=150\text{°C}$	Q_{rr}	-	970	-	nC
Reverse recovery softness factor $V_R=400\text{V}$, $I_F=23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=25\text{°C}$ $V_R=400\text{V}$, $I_F=23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=125\text{°C}$ $V_R=400\text{V}$, $I_F=23\text{A}$, $di_F/dt=1000\text{A}/\mu\text{s}$, $T_j=150\text{°C}$	S	-	4.4	-	

1 Power dissipation

$P_{tot} = f(T_C)$

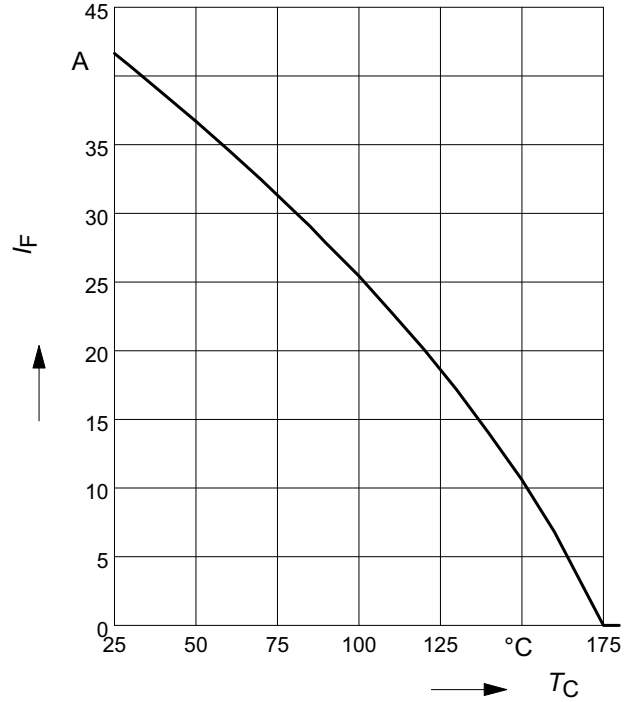
parameter: $T_j \leq 175\text{ °C}$



2 Diode forward current

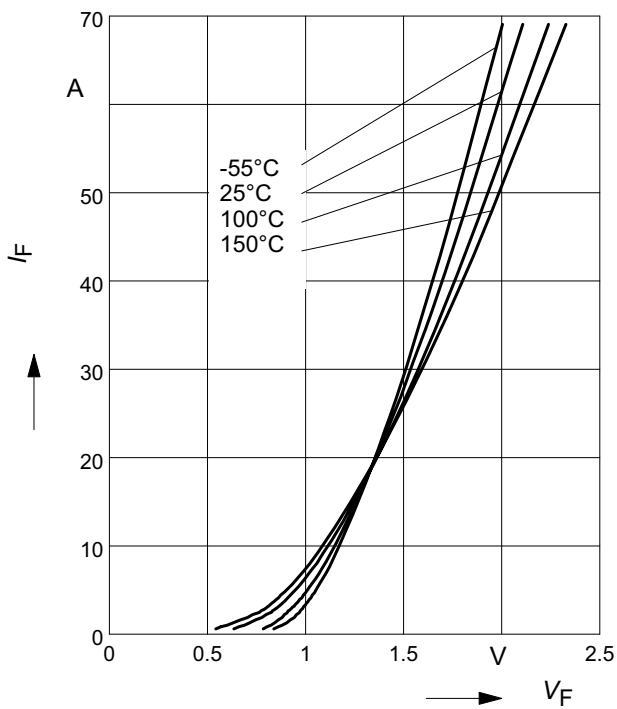
$I_F = f(T_C)$

parameter: $T_j \leq 175\text{ °C}$



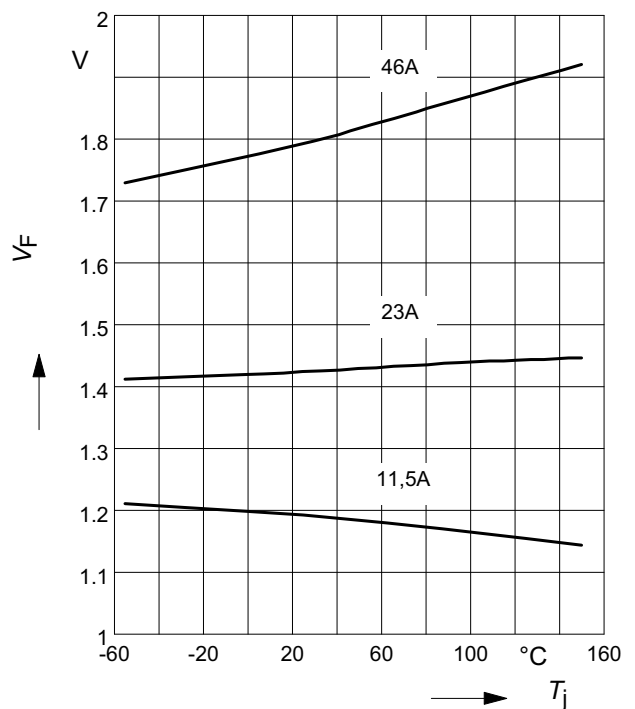
3 Typ. diode forward current

$I_F = f(V_F)$



4 Typ. diode forward voltage

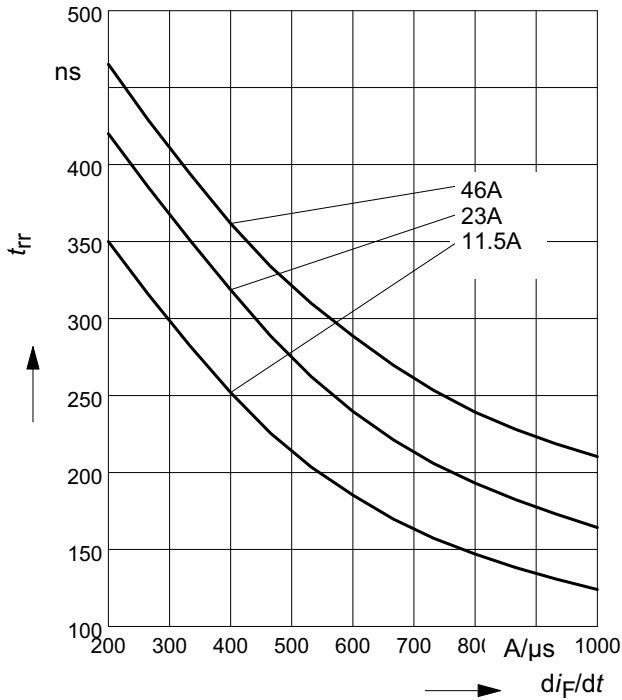
$V_F = f(T_j)$



5 Typ. reverse recovery time

$$t_{rr} = f(dI_F/dt)$$

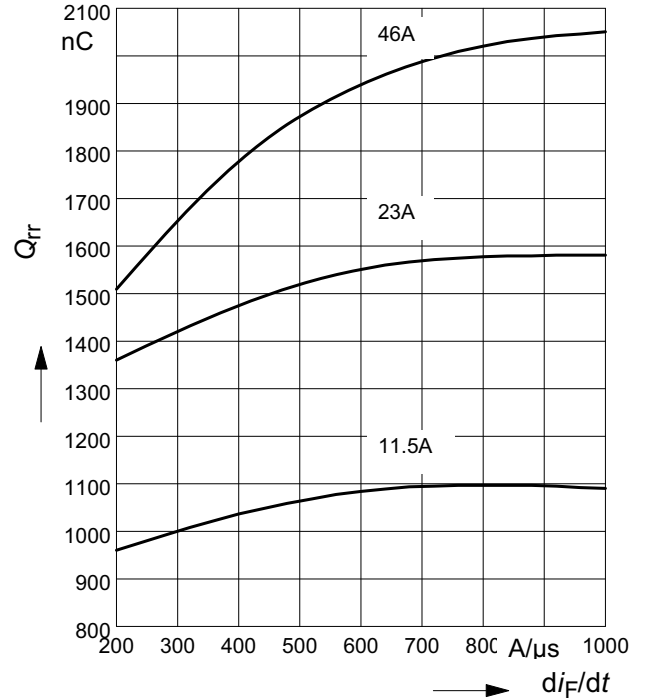
parameter: $V_R = 400V, T_j = 125^\circ C$



6 Typ. reverse recovery charge

$$Q_{rr} = f(dI_F/dt)$$

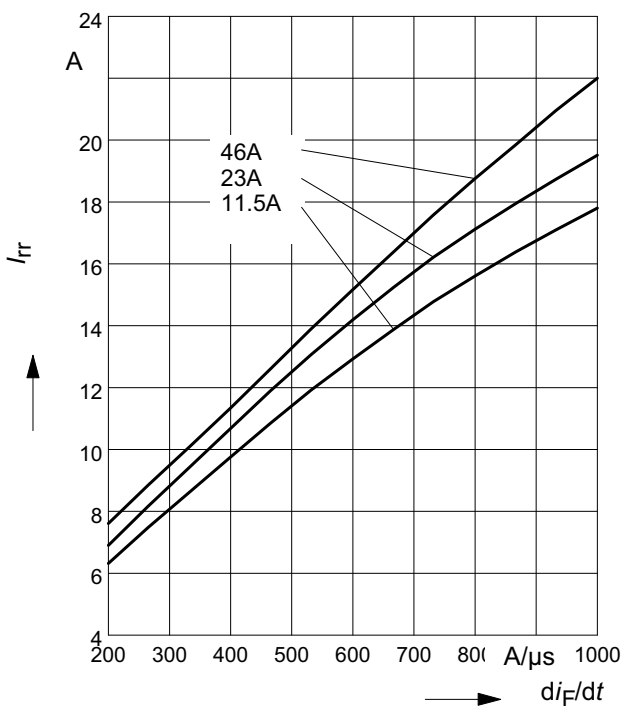
parameter: $V_R = 400V, T_j = 125^\circ C$



7 Typ. reverse recovery current

$$I_{rr} = f(dI_F/dt)$$

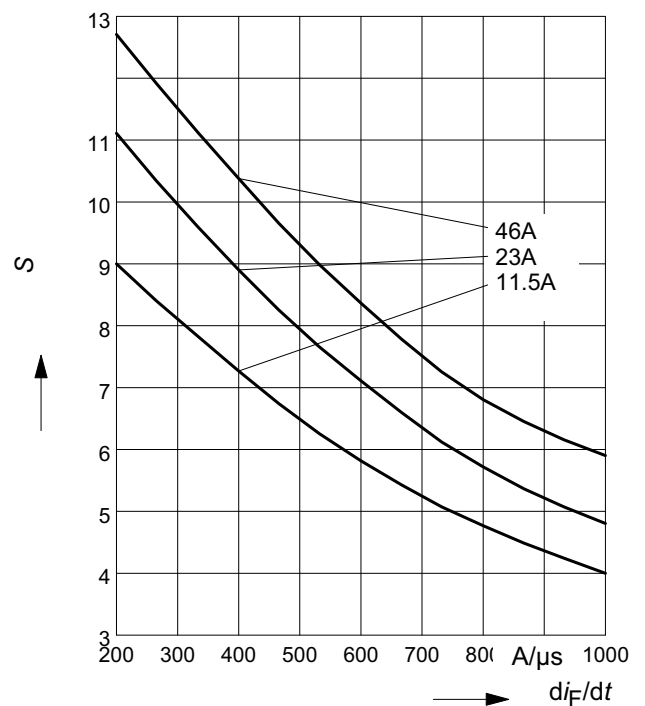
parameter: $V_R = 400V, T_j = 125^\circ C$



8 Typ. reverse recovery softness factor

$$S = f(dI_F/dt)$$

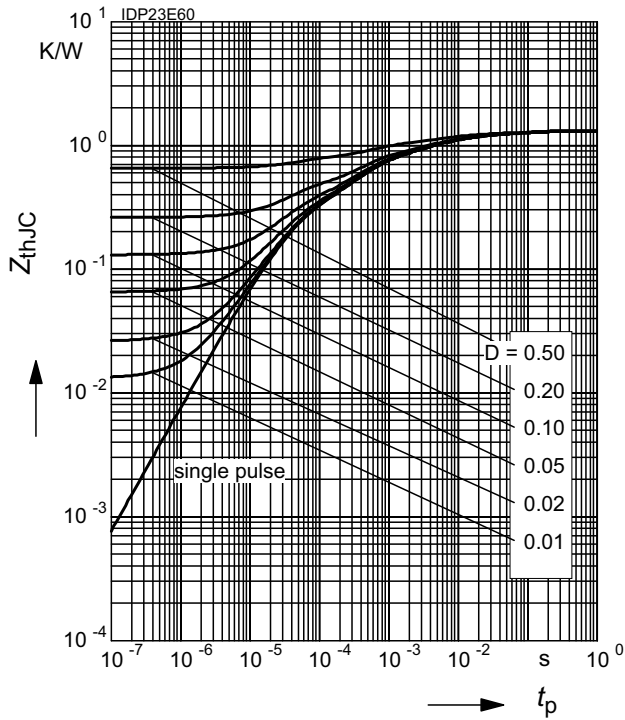
parameter: $V_R = 400V, T_j = 125^\circ C$



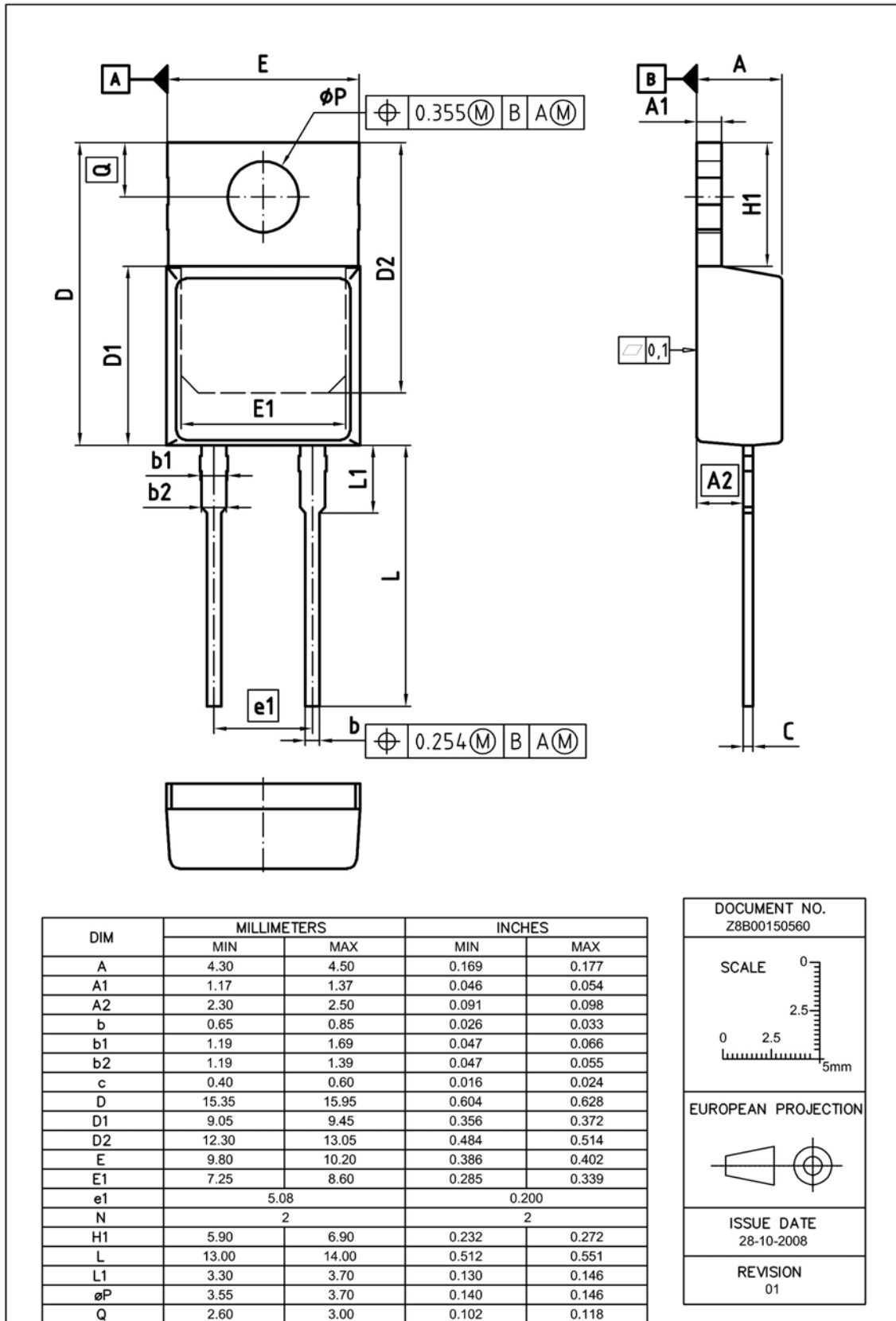
9 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

parameter : $D = t_p/T$



Outline drawing: TO220-2-1



Published by
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81726 München, Germany
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